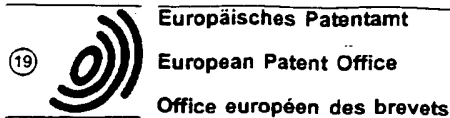


EP 19255 (C)



(11) Publication number : **0 680 079 A2**

(12)

## EUROPEAN PATENT APPLICATION

(21) Application number : **95302614.3**

(51) Int. Cl.<sup>6</sup> : **H01L 21/321, G02F 1/133**

(22) Date of filing : **19.04.95**

(30) Priority : **28.04.94 US 235010**

(43) Date of publication of application :  
**02.11.95 Bulletin 95/44**

(84) Designated Contracting States :  
**DE FR GB**

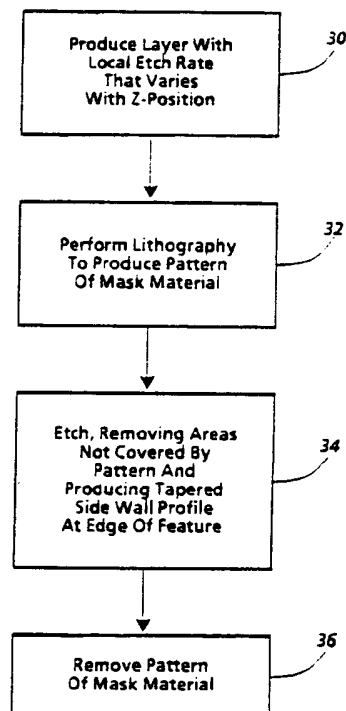
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(54) **Thin-film structure tapered feature.**

(57) A feature (18; Fig.1) in a thin-film structure (16; Fig.1) such as an AMLCD array (Fig.6) has an edge with a tapered sidewall profile (24; Fig. 1), reducing step coverage problems. The method of forming the feature includes producing (30) a layer in which local etch rates vary in the thickness direction of the layer. The layer can then be etched (34) to produce the feature with the tapered sidewall profile. The layer can be produced by physical vapor deposition. The layer can, for example, include sublayers with different etch rates (Fig.9), either due to different atomic proportions of constituents or due to different etchants. Or local etch rates can vary continuously as a result of changing deposition conditions. Differences in etch rates or differences in etchant mixtures can be used to obtain a desired angle of elevation.



**Fig. 5**

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The present invention relates to thin-film structures, and their method of manufacture.

It is known to produce a thin-film structure with a feature that is tapered. Tapering may be useful to reduce problems with step coverage. Reverse tapering may be useful in performing liftoff techniques. Resist erosion by plasma etching has been used to produce tapering.

The invention provides a thin-film structure at a surface of a substrate, and the thin-film structure includes a tapered feature such as a tapered line or a tapered lead. Tapering is achieved by differentially etching a layer within which local etch rate varies.

The present invention provides a method of forming a thin-film structure at a surface of a substrate; the method comprising: performing deposition to produce a first layer with a first side toward the surface of the substrate and a second side away from the surface of the substrate; the first layer extending in a thickness direction from the first side to the second side; the first layer having a local etch rate for an etchant that varies with position in the thickness direction; performing lithography to produce a pattern of mask material: the pattern including a part that covers part of the first layer; the covered part of the first layer having the shape of a feature; and etching to remove areas not covered by the pattern of mask material so that the covered part of the first layer forms a feature with an edge extending between the first and second sides of the first layer; the act of etching further etching the edge of the feature with the etchant so that the edge has a sidewall profile that is tapered.

The invention further provides a thin film device obtainable by the method of any of claims 1 to 8.

The invention further provides a thin film device according to claims 8 or 9 of the appended claims.

Preferably, the feature is a conductive line. Preferably, the feature comprises a first element and a second element, the atomic ratio of the first and second elements varying in the thickness direction.

Preferably, the first and second elements are metals. Preferably, the first element is molybdenum and the second element is chromium. The atomic ratio of molybdenum to chromium at the first side may be approximately 83/17 and the atomic ratio of molybdenum to chromium at the second side approximately 87/13; the sidewall profile having an angle of elevation of approximately 60°. Alternatively, the atomic ratio of molybdenum to chromium at the first side may be approximately 85/15 and the atomic ratio of molybdenum to chromium at the second side approximately 60/40; the sidewall profile having an angle of elevation of approximately 6°.

The atomic ratios of the first and second elements may vary continuously across the feature from the first side to the second side.

Preferably, the feature includes a first sublayer at the first side and a second sublayer at the second

side; the first sublayer having a first atomic ratio with a first local etch rate and the second sublayer having a second atomic ratio with a second local etch rate; the first and second local etch rates being different.

Preferably, the first local etch rate is slower than the second local etch rate. Preferably, the etchant includes a first fluid and a second fluid, the first fluid etching the first sublayer and the second fluid etching the second sublayer.

The feature preferably further includes a third sublayer between the first and second sublayers; the third sublayer having a third local etch rate that is between the first and second local etch rates.

The feature may include three or more sublayers, with the sublayers alternating between sublayers with a first local etch rate and sublayers with a second local etch rate; the first and second local etch rates being different.

Preferably, the sublayers with the first local etch rate comprise aluminum; the first local etch rate being faster than the second local etch rate. Preferably, the sublayers with the second local etch rate comprise titanium-tungsten.

The sidewall profile may have an angle of elevation less than 60°, less than 30°, or less than 6°.

Tapering can solve problems that arise in producing thin-film structures. For example, an array of light control units for a flat panel display, such as an active matrix liquid crystal display (AMLCD), typically includes two sets of orthogonal metal lines separated by dielectric layers at crossovers. For low line resistivity, a thickness of the metal lines approaching or exceeding that of the dielectric layers between the lines may be necessary. Wet etching is a reliable process for producing the bottom metal lines, but conventional wet etch techniques would produce a step-shaped sidewall profile at each edge of each bottom metal line, a profile which may approach vertical with overetch.

The dielectric layers and the top metal lines that cross the bottom metal lines must therefore cover a large number of steps in an array of usual size, which may result in defects. For example, a layer of silicon oxide or nitride crossing over a step-shaped AMLCD scan line is likely to crack if the scan line is thicker than about 1500 angstroms (150nm). This constraint on the maximum thickness produces an undesirably high resistivity for many metals used in scan lines, a problem which becomes more severe as the panels become larger. With lines over 25 cm long, for example, the RC delay and line voltage drop from one end of a line to the other can compromise a display's performance.

If scan lines are appropriately tapered, however, the layer of silicon oxide or nitride is unlikely to crack even at significantly larger thicknesses. Therefore, tapered lines can be made sufficient thick to bring resistivity down to satisfy a display's performance re-

quirements. But despite these advantages, tapering is difficult to achieve. Processes such as resist lifting, resist erosion such as with plasma etching, and spacer formation could be used to produce tapering but are difficult to control and therefore do not produce tapered features robustly and reliably.

The invention provides a number of techniques that can produce tapered features robustly and reliably by differentially etching a layer within which local etch rate varies. The techniques vary local etch rates by varying deposition conditions, by varying materials, or by a combination of varying materials and deposition conditions. Depending on the complexity of the materials used, the techniques may require appropriate mixtures of chemical etchants to obtain a desired taper. In general, the techniques can be used to obtain a sidewall profile with any desired angle of taper.

The invention has been implemented to produce a 5000 angstrom (500nm) thick MoCr scan line with a taper angle of 60 degrees, over which a nitride layer did not crack. The tapered MoCr scan line had a measured resistance of approximately 0.6 ohms/sq, comparable to a step-shaped 1000 angstrom (100nm) layer of pure aluminum, while a step-shaped 1000 angstrom (100nm) thick MoCr scan line would have a measured resistance of 3.0 ohms/sq. Several other taper angles have been demonstrated, including 30 degrees and 6 degrees.

The invention can be implemented by producing a layer within which local etch rate varies with position in the z-direction, the direction perpendicular to the substrate's surface. Then, a pattern of mask material can be formed using lithographic techniques, and an etching operation can remove areas not covered by the pattern. The etching operation also produces taper at the boundary between an area covered by the pattern and an adjacent area that is not covered, producing a tapered feature. Then, the pattern of mask material can be removed.

One of the techniques provides a thick sublayer with a slower local etch rate, capped by a thin sublayer with a faster local etch rate. Each sublayer may be an alloy, with all the alloys including the same materials, but in different proportions or deposited under different conditions to obtain different local etch rates with the same etchant. After etching, the thick sublayer has a tapered sidewall profile while the thin sublayer's profile is not significantly tapered. The local etch rates of the sublayers can be adjusted to obtain different angles of taper. If necessary, the thin capping sublayer could be removed after etching to obtain a more evenly tapered profile.

Another technique provides alternating sublayers of two materials that etch at different rates with different etchants that can be mixed. Each layer of the slower etching material delays the start of etching of layers below it. As a result, the layers of faster etch-

ing material etch for different periods of time, producing a tapered sidewall profile. The layers of slower etching material can be thin enough to be fully etched away once the faster etching material has been etched. Alternatively, remaining parts of the layers of slower etching material can be removed by a subsequent etching operation. The proportions of etchants in the mixed etchant can be adjusted to obtain a desired angle of taper.

The invention is advantageous compared to other techniques that could be used to produce tapered features. In comparison with photoresist lifting, the invention is more robust because photoresist lifting relies on a failure mechanism of resist adhesion, a failure mechanism that is hard to control and that can produce poorly defined boundaries. In comparison with plasma etching to produce resist erosion, the invention is more reliable because it is easier to control and much more uniform over large areas. In comparison with spacer formation, the invention is simpler and more reliable.

Embodiments of the invention will now be described, by way of example, with reference to the accompanying drawings, in which:

Fig. 1 is a schematic cross-section of a thin-film structure that includes a tapered feature within which local etch rate varies in the thickness direction;

Fig. 2 is a graph showing local etch rate as a function of position in the thickness direction in a layer in which local etch rate varies continuously;

Fig. 3 is another graph showing local etch rate as a function of position in the thickness direction in a layer that includes two sublayers with different local etch rates;

Fig. 4 is another graph showing local etch rate as a function of position in the thickness direction in a layer that includes alternate sublayers with different local etch rates;

Fig. 5 is a flow chart showing general steps in producing a thin-film structure with a tapered feature within which local etch rate varies;

Fig. 6 is a schematic plan view of a layout of an array of light control units with tapered conductive lines;

Fig. 7 is a plan view of a layout of a light control unit in an implementation of the array of Fig. 3;

Fig. 8 is a schematic view of a sputtering chamber with two molybdenum-chromium targets;

Fig. 9 is a graph showing etch rate as a function of atomic proportions of molybdenum and chromium and of etch temperature;

Fig. 10 is a flow chart showing acts in producing a tapered conductive line that includes molybdenum and chromium;

Fig. 11 shows sequential stages in producing a tapered conductive line as in Fig. 10;

Fig. 12 is a scanning electron microscope view of

a cross-section of a tapered line produced as in Fig. 10;

Fig. 13 is a scanning electron microscope view of a cross-section of another tapered line produced as in Fig. 10;

Fig. 14 is a scanning electron microscope top view of a tapered line produced as in Fig. 10;

Fig. 15 is a schematic view of a sputtering chamber with an aluminum target and a titanium-tungsten target;

Fig. 16 is a schematic cross-section view of a layer that includes multiple sublayers, produced in the chamber of Fig. 15;

Fig. 17 is a graph showing etch rate as a function of ratios of etchants in a mixture and of etch temperature;

Fig. 18 is a scanning electron microscope view of a cross-section of a tapered feature produced from a layer as in Fig. 16;

Fig. 19 is a scanning electron microscope top view of another tapered feature produced from a layer as in Fig. 16 but with a different ratio of etchants than Fig. 18; and

Fig. 20 is a graph showing etch rate as a function of gas pressure during deposition;

As used herein, "etch rate" is a rate at which an etching operation removes material. A "local etch rate" is an etch rate in a region of a layer or part of a layer in which etch rates vary. An etch rate "for an etchant" is an etch rate for an etching operation that uses the etchant.

A feature has a local etch rate for an etchant that "varies with position in the thickness direction" in a feature if the local etch rate for the etchant within the feature is a function of position in the thickness direction.

The "sidewall profile" of an edge of a feature is the profile that extends between the feature's first side and the feature's second side at the edge, and can be viewed by taking a section of the edge.

The sidewall profile of an edge of a feature in a thin-film structure formed at a surface of a substrate is "tapered" if the projection of the line at which the sidewall profile meets the feature's second side is not the same as the line at which the sidewall profile meets the feature's first side.

The "angle of elevation" of a sidewall profile is the angle formed at the line at which the sidewall profile meets the feature's first side between the surface of the substrate extending under the feature and the surface of the sidewall extending to the line at which the sidewall profile meets the feature's second side. If the sidewall is not planar, the "angle of elevation" may be an approximation obtained locally by treating the sidewall's surface as the plane that includes the local line segments at which the sidewall profile meets the feature's first and second sides.

An "alloy" is a material that is a macroscopically

homogeneous mixture of two or more metals.

In an alloy or other mixture of two or more elements, the relationship between the quantities of atoms of the elements can be expressed as an "atomic percent," an "atomic proportion," or an "atomic ratio."

Figure 1 shows a thin-film structure that includes a feature with a tapered sidewall profile at an edge, Fig. 2 shows how local etch rate can vary continuously in the thickness direction of a layer, Fig. 3 shows how local etch rate can differ in two sublayers of a layer, Fig. 4 shows how local etch rate can differ in alternate sublayers of a layer, and Fig. 5 shows general acts in producing a feature with a tapered sidewall profile at an edge.

Product 10, shown in cross-section in Fig. 1, includes substrate 12 with surface 14 at which thin-film structure 16 is formed. Thin-film structure 16 includes feature 18 with first side 20 toward surface 14, second side 22 away from surface 14, and edge 24 extending between first side 20 and second side 22. Feature 18 could be on surface 14 but, as suggested by the ellipses in Fig. 1, thin-film structure 16 can also include one or more layers between feature 18 and surface 14. Thin-film structure 16 can also include one or more layers above feature 18.

Feature 18 can be etched by an etchant, and the local etch rate for the etchant varies in the thickness or z-direction from first side 20 at  $z_0$  to second side 22 at  $z_1$ . As a result of the varying local etch rate, the sidewall profile of edge 24 has been tapered by an etching operation using the etchant, and has an angle of elevation  $\theta$  that is not equal to  $90^\circ$ .

The curve in Fig. 2 shows one way in which local etch rate could vary as a function of  $z$  between  $z_0$  and  $z_1$ . The local etch rate curve in Fig. 2 begins at a minimum at  $z_0$  and increases monotonically to a maximum at  $z_1$ . Although it may be possible to obtain a continuously varying local etch rate curve as illustrated in Fig. 2 by varying conditions of deposition or by continuously changing proportions of materials in a layer, a continuously varying local etch rate curve may be difficult to achieve in practice.

The curve in Fig. 3 shows another way in which local etch rate could vary as a function of  $z$ . Rather than increasing monotonically, as in Fig. 2, the etch rate curve in Fig. 3 increases discontinuously at a boundary  $z_i$  between layers. As discussed below, the sublayer under  $z_i$  is a thick sublayer with a slow etch rate, but the sublayer above is a thin capping sublayer with a fast etch rate.

The curve in Fig. 4 shows another way local etch rate could vary. In this case, the local etch rate curve increases at some boundaries between sublayers and decreases at others, because the layer includes sublayers that alternate between a fast local etch rate and a slow local etch rate. This local etch rate curve produces a tapered sidewall profile because of differ-

ences in etch time at different sublayers, as discussed in more detail below.

In Fig. 5, the process begins with the step 30 of performing deposition to produce a layer with a local etch rate for an etchant, the local etch rate varying in the thickness or z-direction of the layer. The step 30 could produce a layer with a local etch rate curve as illustrated in Figs. 2-4 or with another type of local etch rate curve. Next, at step 32, lithography is performed to produce a pattern of mask material that covers a part of the layer that has the shape of a feature. The following step 34 is an etch to remove areas not covered by the pattern of mask material from box 32. As a result of the etch 34, the covered part of the layer forms a feature with an edge. The step 34 also etches the edge with the etchant so that the edge's sidewall profile is tapered. Then step 36 removes the pattern of mask material.

The general features described above could be implemented in numerous ways to provide a thin-film structure with a tapered feature on a surface of a substrate.

Figure 6 shows a partial layout of an array with tapered scan lines; and Fig. 7 shows a layout of a light control unit in the array of Fig. 6.

Array 70 in Fig. 6 includes scan lines 72, 74, through 76 and data lines 80, 82, through 84. Scan lines 72, 74, through 76 are tapered conductive lines, with scan lines 74 through 76 each connected to a row of light control units to provide a signal selecting the light control units in that row. Illustrative light control unit 90, for example, receives its signal from scan line 74.

In some implementations, each light control unit in array 70 could be receive a binary signal from its scan line, so that the light control unit is driven either in its fully ON saturation state or in its fully OFF saturation state. Alternatively, each light control unit could receive a multi-level signal that can indicate three or more gray levels. In either case, conductivity of scan lines is important--as conductivity declines, the scan signal becomes damped and delayed, causing problems with delay of binary signals or with damping of non-saturation gray levels. Tapered conductive lines can provide sufficient conductivity to alleviate this problem because they can be thicker than conductive lines with edges that have step-shaped sidewall profiles.

Figure 7 shows a light control unit. Fig. 7 shows several layers of a thin-film structure, with upper layers that are farthest from the substrate's surface obscuring lower layers.

The uppermost layer shown in Fig. 7 is a top metal layer, which forms data line 110 connected to a channel lead of a transistor in the light control unit; the top metal layer also forms several other features described below. The next layer shown is a layer of indium-tin-oxide (ITO), which forms transparent electrode

112. The next layer is a top nitride layer, which forms island 114, part of the transistor. The lowest layer shown is a bottom metal layer, which forms gate line 116 and, connected to it, gate lead 118, which serves as the gate lead of the transistor.

Data line 110 can be implemented with a resistance of 0.2 ohm/sq. and can be driven at - 8 V, 0 V, and + 8 V. Data line 110 provides a data signal to a column of binary control units, one of which is shown in Fig. 4. The part of data line 110 that extends over gate lead 118 connects to the source lead of the transistor.

Gate line 116 similarly provides a scan signal to a row of binary control units. Gate line 116 can be formed with a resistance of 1.4 Ohm/Sq and can be driven at + 15 V and - 15 V.

Data line 110 and gate line 116 are each 10  $\mu$ m wide. Data line 110 crosses over gate line 116 in crossover region 120. Crossover region 120 can include an insulator formed by the top nitride layer, and other features as necessary to ensure that the two lines conduct signals adequately and that signals in the two lines do not interfere.

Transparent electrode 112 connects to the drain lead of the transistor through drain line 122, formed by the top metal layer. Therefore, when the transistor is conductive due to a scan signal provided to gate lead 118 by gate line 116, transparent electrode 112 receives and stores a drive signal from data line 110 through drain line 122.

Transparent electrode 112 also connects to charging lead 124, which forms one electrode of a storage capacitor and is formed by the top metal layer. Gate line 126, formed by the bottom metal layer, forms the other electrode of the storage capacitor; gate line 126 also provides a scan signal to the preceding binary control unit in the same column.

Figure 8 shows how two sputtering targets can be used to produce a layer with local etch rates as in Fig. 3. Fig. 9 illustrates etch rate as a function of atomic proportions of molybdenum and chromium. Fig. 10 shows acts in producing a layer using two targets as in Fig. 8. Fig. 11 illustrates stages in etching a layer produced as in Fig. 10. Figs 12-14 show actual features with tapered sidewall profiles at their edges, produced by acts as in Fig. 10.

Chamber 140 in Fig. 8 can be the vacuum chamber of a conventional magnetron sputtering machine. In chamber 140 are target 142, a first alloy target of  $\text{Mo}(x_1)\text{Cr}(y_1)$ , and target 144, a second alloy target of  $\text{Mo}(x_2)\text{Cr}(y_2)$ , where  $y_n = (1 - x_n)$  and where  $(x_n/y_n)$  is the atomic ratio of molybdenum to chromium in a molybdenum-chromium alloy. Substrate 146 is within chamber 140, mounted so that it can be moved back and forth between a first position adjacent target 142 for deposition of the first alloy and a second position adjacent target 144 for deposition of the second alloy. Sputtering can be performed using conventional

techniques, as described in EP-A-000,000, corresponding to U.S. application S.N. 08/235,008, filed 28th April 1994, entitled "Thin-Film Structure With Conductive Molybdenum-Chromium Line".

Figure 9 illustrates etch rates, measured in angstroms per second, for different Mo(x)Cr(y) alloys at different etch temperatures, illustrating why two different alloys can be used to produce sublayers with different local etch rates. As shown, at an etch temperature of 50° C, etch rates fall almost linearly from around 15 atomic percent molybdenum to around 30 atomic percent molybdenum, then rise almost linearly. At an etch temperature around room temperature, illustratively 22° C, etch rates fall from around 15 atomic percent molybdenum to around 25 atomic percent molybdenum, then remain almost constant. It is possible to obtain a ratio between etch rates greater than 3:1 between two sublayers with different atomic proportions of molybdenum.

Referring to Fig. 10, the process of producing a tapered conductive line begins with the step 160 of performing physical vapor deposition (PVD) to produce a first sublayer that includes Mo(x<sub>1</sub>)Cr(y<sub>1</sub>). Next (step 162) physical vapor deposition (PVD) to produce a second sublayer that includes Mo(x<sub>2</sub>)Cr(y<sub>2</sub>), where x<sub>1</sub> > x<sub>2</sub> so that the local etch rate of the second sublayer is significantly faster than the local etch rate of the first. Together the first and second sublayers form a layer that include molybdenum and chromium, with each sublayer including an MoCr alloy, and with a local etch rate that varies with position in the thickness direction. The steps 160 and 162 can be implemented using the arrangement in Fig. 8, by first positioning substrate 146 for sputtering from target 142 to produce the first sublayer, then moving substrate 146 to position is for sputtering from target 144 to produce the second sublayer.

Step 164 is lithography to produce a pattern of mask material that covers a part of the layer of molybdenum and chromium that has the shape of a feature. The next step 166 is an etch to remove areas not covered by the pattern of mask material in step 164. As a result of the etching operation in step 166, the covered part of the MoCr layer forms a feature that includes molybdenum and chromium. In addition, the etch of step 166 differentially under the pattern boundary to produce an edge of the feature with a tapered sidewall profile. Then, in step 168 the pattern of mask material is removed from the feature.

Figure 11 shows stages of step 166 in Fig. 10. In the first stage, before etching begins, layer 180 is on substrate 146, with sublayers 182 and 184. Layer 180 can be 5000 angstroms (500nm) thick, for example, with sublayer 182 being 4600 angstroms (460nm) thick and 83 atomic percent molybdenum, while sublayer 184 is a thin capping sublayer 400 angstroms (40nm) thick and 87 atomic percent molybdenum. These atomic proportions result in an etch ratio of ap-

proximately 2.5 at room temperature, as can be seen from Fig. 9. Resist 186 covers part of layer 180 with the shape of a feature to be produced.

After etching begins, as shown in the second stage in Fig. 11, sublayer 184 is quickly etched away in areas that are not covered by resist 186, and then begins to etch away under resist 186, as illustrated by intermediate sidewall 190. Because sublayer 184 is etched away, part of sublayer 182 under resist 186 is exposed to the etchant and is etched, but not as deeply as in areas not covered by resist 186 because the etching period is shorter.

Finally, when the etchant has etched through sublayer 182 in areas not covered by resist 186, non-tapered sidewall 192 of sublayer 184 and tapered sidewall 194 of sublayer 182 together form the sidewall profile of the resulting feature, as shown in the third stage in Fig. 11.

After the third stage in Fig. 11, resist 186 can be removed by the act in box 168 in Fig. 10. Sublayer 184 could also be a sacrificial layer that is removed by an appropriate operation to obtain a more uniformly tapered sidewall profile.

Figure 12 shows a scanning electron microscope (SEM) image of a cross-section of a conductive line produced by acts as in Fig. 10, with the first sublayer being 4600 angstroms (460nm) and having 75 atomic percent of molybdenum and with the second sublayer being 400 angstroms (40nm) and having 60 atomic percent of molybdenum. The line is approximately 15 μm wide and 0.5 μm thick. As shown, the resulting angle of elevation of the sidewall profile at each edge of the conductive line is approximately 30°.

Figure 13 shows an SEM image of a cross-section of another conductive line produced by acts as in Fig. 10, with the first sublayer being 4600 angstroms (460nm) and having 85 atomic percent of molybdenum and with the second sublayer being 400 angstroms (40nm) and having 60 atomic percent of molybdenum. The line is approximately 15 μm wide and 0.5 μm thick. As shown, the resulting angle of elevation of the sidewall profile at each edge of the conductive line is approximately 6°.

Figure 14 shows an SEM image of an arrangement of conductive lines produced by acts as in Fig. 10, with the same angle of elevation as in Fig. 13. Tapering can be seen at the periphery of each line.

Figures 12-14 show that edges with tapered sidewall profiles have been successfully produced using the two sublayer technique described above. In addition, chemical vapor deposition of a dielectric layer of silicon nitride over conductive lines as illustrated in Figs. 12-14 and also with angles of elevation of 60° have shown conformal coverage with no problem at the edge of a conductive line.

Figure 15 shows how two sputtering targets can be used to produce a layer with local etch rates as in Fig. 4. Fig. 16 shows a cross-section of a layer pro-

duced with the arrangement in Fig. 15. Fig. 17 illustrates etch rates of aluminum and titanium-tungsten as a function of etchant proportions at several temperatures. Figs. 18 and 19 show actual features with tapered sidewall profiles at their edges, produced with the arrangement in Fig. 15.

Chamber 210 in Fig. 15 can be the same as in Fig. 8, but with target 212 aluminum and target 214 an alloy target of titanium and tungsten. An alloy target with commonly used proportions such as 10 percent titanium by weight could be used. Substrate 216 is within chamber 210, mounted so that it can be moved back and forth between a first position adjacent target 212 for deposition of aluminum and a second position adjacent target 214 for deposition of titanium-tungsten. Sputtering can be performed using conventional techniques, following the same acts as in Fig. 10, but with the steps 160 and 162 being replaced by a series of acts, each producing one of a number of sublayers and with alternate sublayers being aluminum, the aluminum sublayers being separated by titanium-tungsten sublayers.

Figure 16 shows substrate 216 with layer 230 formed at its surface. Layer 230 includes aluminum sublayers 232, 234, 236, 238, and 240, separated by titanium-tungsten sublayers 250, 252, 254, and 256. Aluminum sublayers 232, 234, and 236 can each be 600 angstroms (60nm) thick, while aluminum sublayer 238 can be 400 angstroms (40nm) thick, and aluminum sublayer 240 can be 200 angstroms (20nm) thick. Titanium-tungsten sublayers 250, 252, 254, and 256 can each be 100 angstroms (10nm) thick.

Figure 17 illustrates etch rates, measured in angstroms per second, for different mixtures of etchants at different etch temperatures, illustrating why materials that are etched by different subetchants can be used to produce sublayers with different local etch rates. The subetchant for titanium-tungsten is  $H_2O_2$ , while that for aluminum is a standard aluminum etchant with  $H_3PO_4$  being the predominant constituent. At an etch temperature of 50° C, a low ratio of  $H_2O_2$  to aluminum subetchant such as 10-30:1 produces significantly different etch rates.

Figure 18 shows an SEM image of a cross-section of a feature produced by etching a layer like that in Fig. 16 using a 30:1 ratio of  $H_2O_2$  to aluminum subetchant. The resulting angle of elevation at the edge of the feature is approximately 52°.

Figure 19 shows an SEM top view of another feature produced by etching a layer like that in Fig. 16 using a 10:1 ratio of  $H_2O_2$  to aluminum subetchant. As can be seen, the angle of elevation in Fig. 19 is significantly smaller than in Fig. 18.

Figures 17 and 18 show that edges with tapered sidewall profiles have been successfully produced using the multiple sublayer technique described above.

The implementations described above use sput-

tering to deposit materials such as molybdenum-chromium, aluminum, and titanium-tungsten. Other physical vapor deposition techniques could be used, such as vacuum evaporation and e-beam deposition.

The implementations described above use materials such as molybdenum-chromium, aluminum, and titanium-tungsten and appropriate etchants for those materials. Other materials and etchants could be used. For example, it may be possible to obtain a tapered dielectric or doped semiconductor feature using the techniques described above.

The implementations described above use particular thicknesses of layers and atomic proportions of materials within layers, but other thicknesses and atomic proportions could be used. In addition, it may be possible to implement the invention with continuously varying etch rates rather than with layers that have different etch rates.

The implementations described above use wet etchants, but dry etchants might also be useful.

The implementations described above use differences in etch rates that result either from differences in atomic proportions of metals in an alloy or from differences in proportions of subetchants in an etchant. Fig. 20 shows etch rates as a function of argon pressure during etching, showing that differences in deposition conditions can produce significant differences in local etch rates in a layer. A further variation would be to dope an elemental metal film with impurities that affect the etch rate, such as an  $N_2$ -Ar mixture in a sputtering gas to incorporate nitrogen into a film of titanium.

The two layer implementation described above uses differences in atomic proportions, but could instead use etch rates that result from differences in proportions of subetchants in an etchant. For example, titanium-tungsten capping layer on an aluminum conductive line could be etched using a mixture of  $H_3PO_4$  and  $H_2O_2$  to obtain tapered sidewall profiles.

The implementations described above produce conductive lines and similar features, but the invention could be used to produce various other features with various shapes and types of tapered sidewall profiles, including reverse tapered features appropriate for liftoff techniques.

The implementations described above are appropriate for an insulating substrate such as glass, but the invention could be implemented in thin-film structures in other types of substrates, such as polysilicon.

The implementations described above employ specific process steps in a specified order. It may be possible to implement the invention with steps in different orders or with other process steps.

The invention could be applied in many ways, including production of an array for an active matrix liquid crystal display (AMLCD). For example, it may be possible to use the invention in producing a scanning array with a thin-film structure or another structure

with conductive lines that connect leads of components.

The invention could also be applied in any conventional process for producing integrated circuits, not just in producing arrays for displays and other purposes.

# Claims

1. A method of forming a thin-film structure at a surface of a substrate; the method comprising:

performing deposition to produce a first layer with a first side toward the surface of the substrate and a second side away from the surface of the substrate; the first layer extending in a thickness direction from the first side to the second side; the first layer having a local etch rate for an etchant that varies with position in the thickness direction;

performing lithography to produce a pattern of mask material; the pattern including a part that covers part of the first layer; the covered part of the first layer having the shape of a feature; and

etching to remove areas not covered by the pattern of mask material so that the covered part of the first layer forms a feature with an edge extending between the first and second sides of the first layer; the act of etching further etching the edge of the feature with the etchant so that the edge has a sidewall profile that is tapered.

2. The method of claim 1, in which the step of performing deposition comprises:

producing a first sublayer with a first local etch rate for the etchant; and

producing a second sublayer with a second local etch rate for the etchant; the first and second local etch rates being different.

3. The method of claim 2, in which the etchant includes a first fluid for etching the first sublayer and a second fluid for etching the second sublayer; the act of etching comprising etching with the first fluid and the second fluid mixed together, the first and second layers for example etching at different local etch rates.

4. The method of claim 2 or 3, in which the step of performing deposition comprises:

producing a third sublayer with a third local etch rate for the etchant; the third sublayer being between the first sublayer and the second sublayer; the third local etch rate being between the first and second etch rates.

5. The method of claim 2, 3 or 4, in which the ta-

pered sidewall profile has an angle of elevation; the angle of elevation depending on (1) the first and second local etch rates, and/or (2) the proportions of the first and second fluids in the etchant.

6. The method of any of claims 2 to 5, further comprising:

after the step of etching, removing the second sublayer.

7. The method of any of the preceding claims in which the step of performing deposition comprises:

producing three or more sublayers, with the sublayers alternating between sublayers with a first local etch rate and sublayers with a second local etch rate; the first and second local etch rates being different.

8. The method of claim 7, in which the etchant includes a first fluid for etching the sublayers with the first local etch rate and a second fluid for etching the sublayers with the second local etch rate; the act of etching comprising etching with the first fluid and the second fluid mixed together.

9. A thin film device, comprising:

a substrate having a surface; and

a thin-film structure formed at the surface of the substrate; the thin-film structure comprising:

a feature with a first side toward the surface of the substrate and a second side away from the surface of the substrate; the feature having an edge extending in a thickness direction from the first side to the second side; the feature having a local etch rate for an etchant that varies with position in the thickness direction; the edge having a sidewall profile that is tapered by an etching operation using the etchant.

10. A thin film device, comprising:

an insulating substrate having a surface; and

a thin-film structure formed at the surface of the insulating substrate; the thin-film structure comprising:

an array of light control units for causing presentation of images; each light control unit having a lead for receiving a unit signal; each light control unit responding to its unit signal by causing presentation of a segment of images presented by the array; and

two or more conductive lines, each comprising first and second metals; each conductive line being connected to the lead of each of a set of the light control units for providing a unit signal to the light control units in the set; each conduc-



tive line having a first side toward the surface of the substrate and a second side away from the surface of the substrate; each conductive line having edges extending in a thickness direction from the first side to the second side; each conductive line having a local etch rate for an etchant that varies with position in the thickness direction; the edges of each conductive line having a sidewall profile that is tapered by an etching operation using the etchant.

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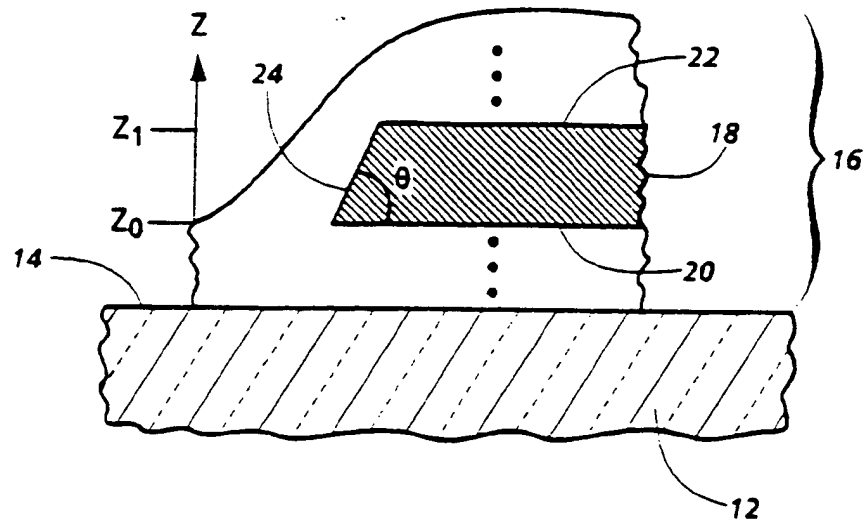
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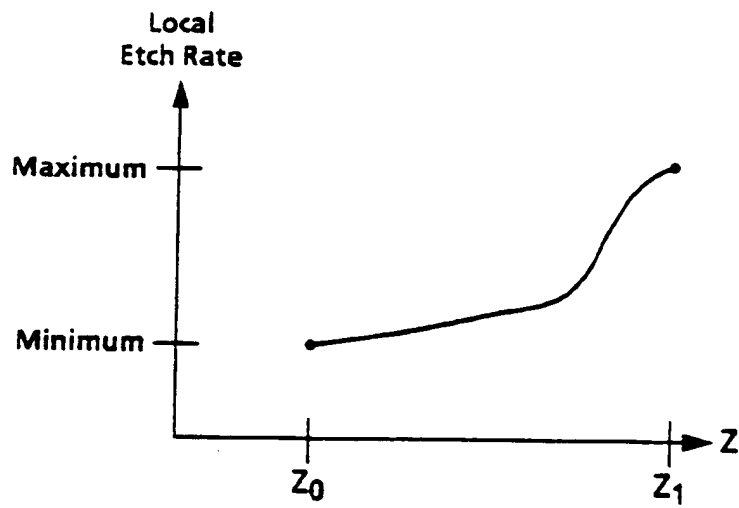
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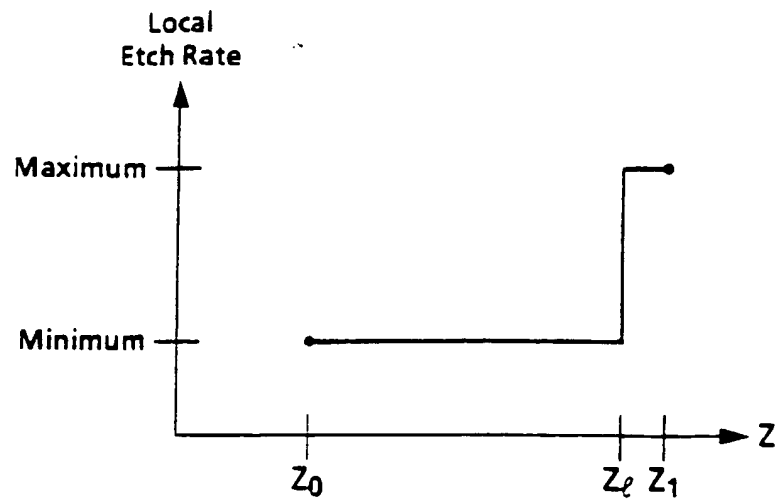
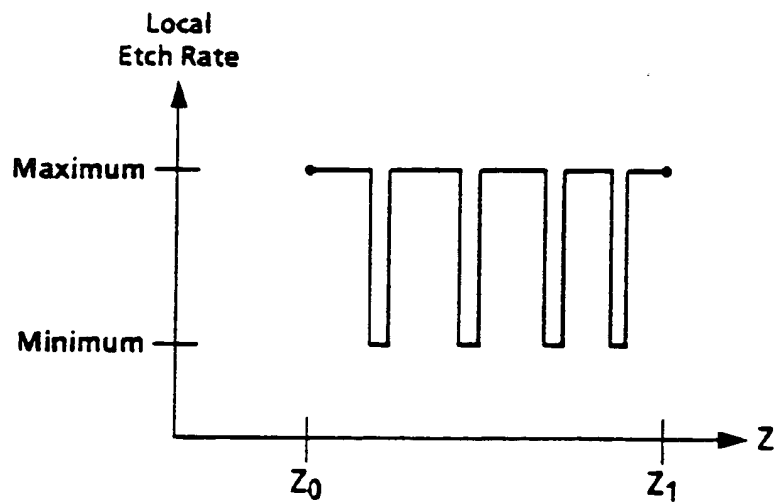
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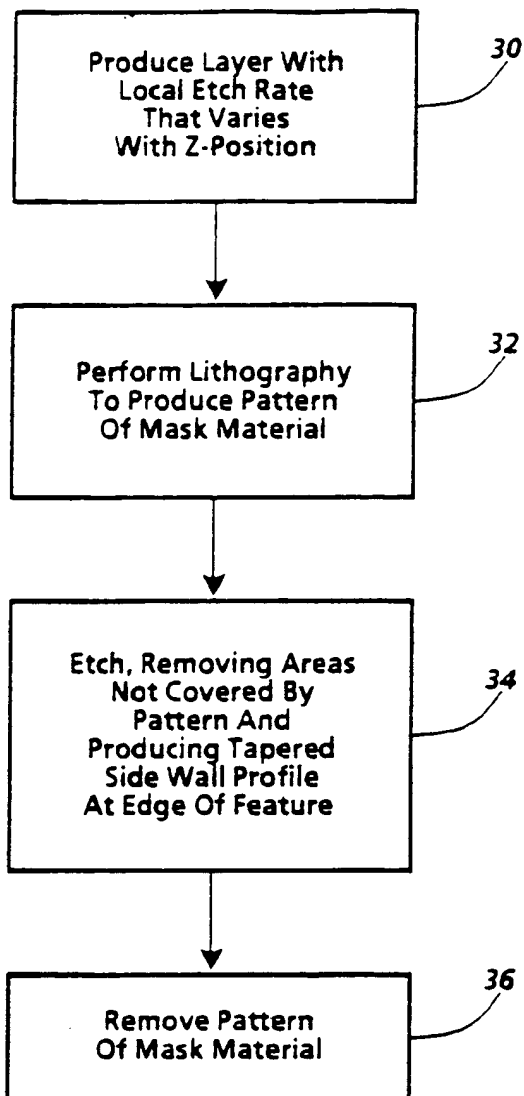


**Fig. 1**

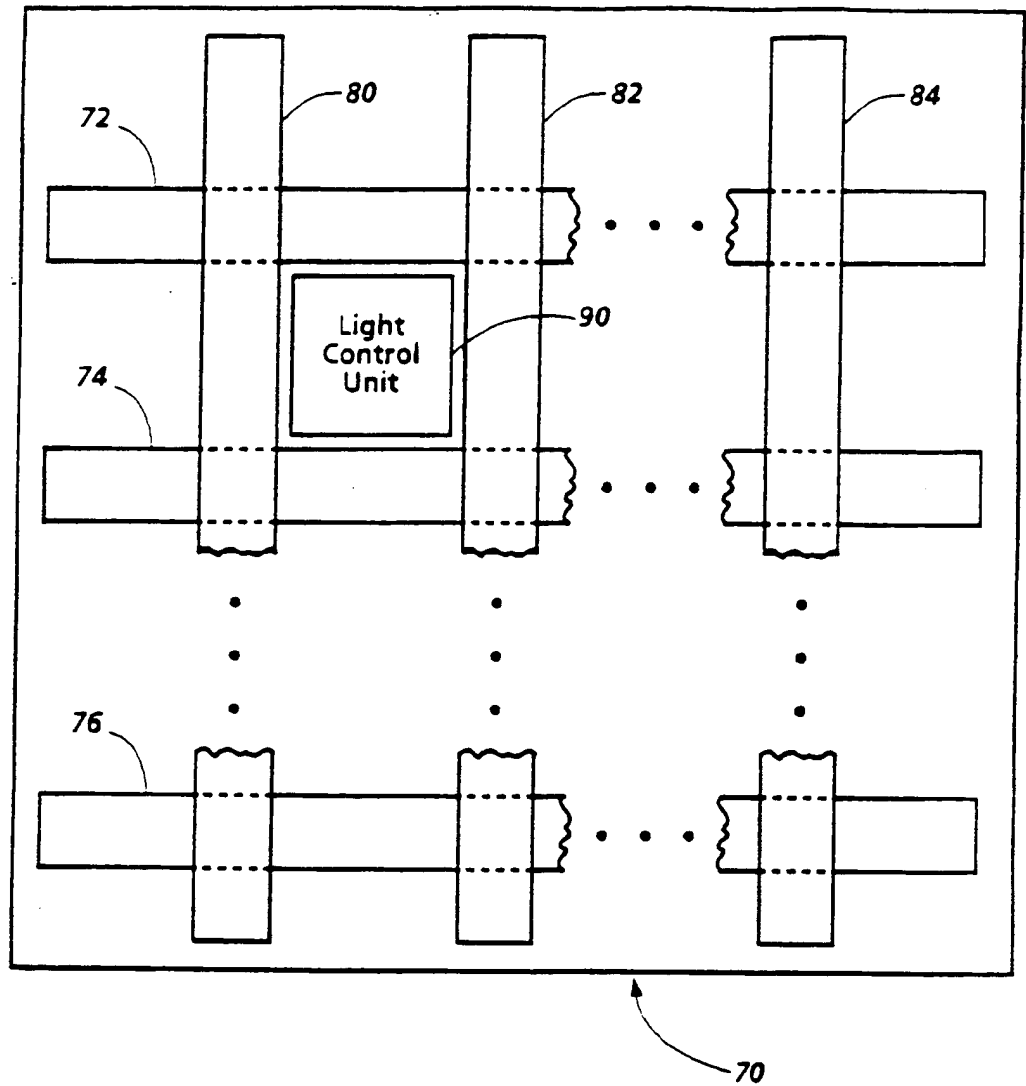


**Fig. 2**

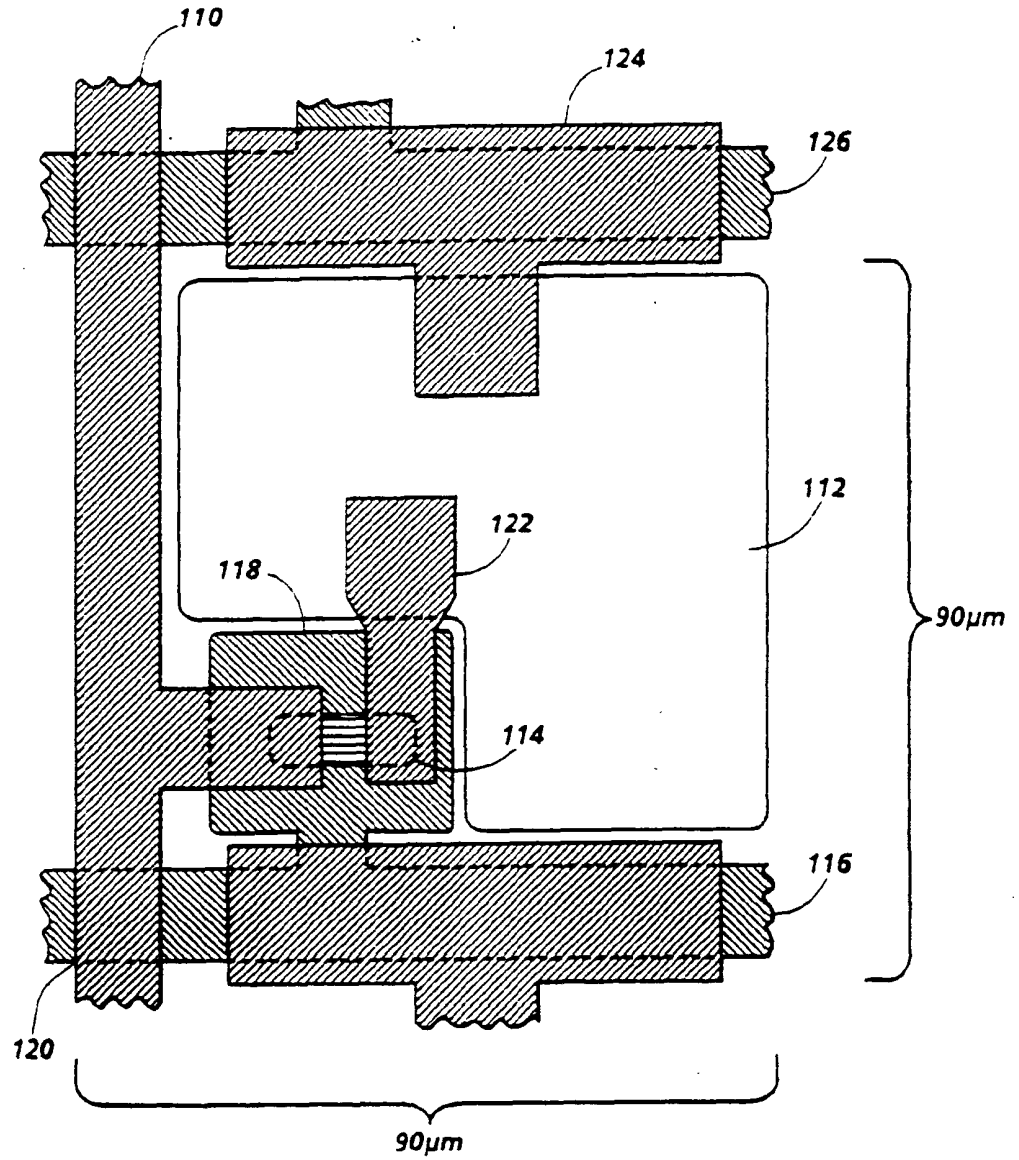
**Fig. 3****Fig. 4**



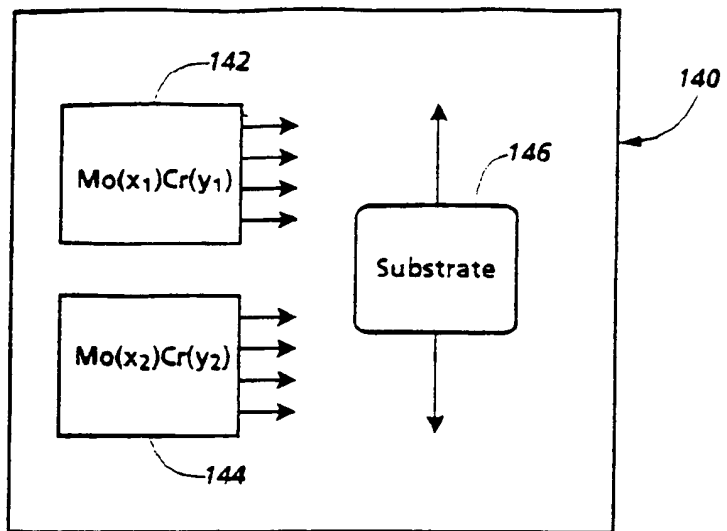
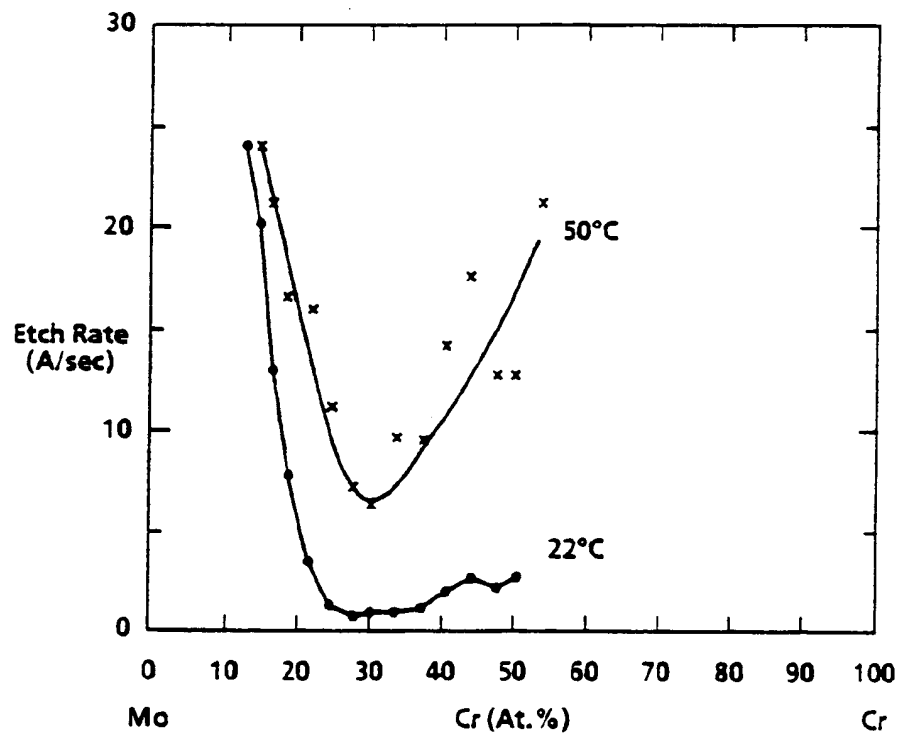
**Fig. 5**

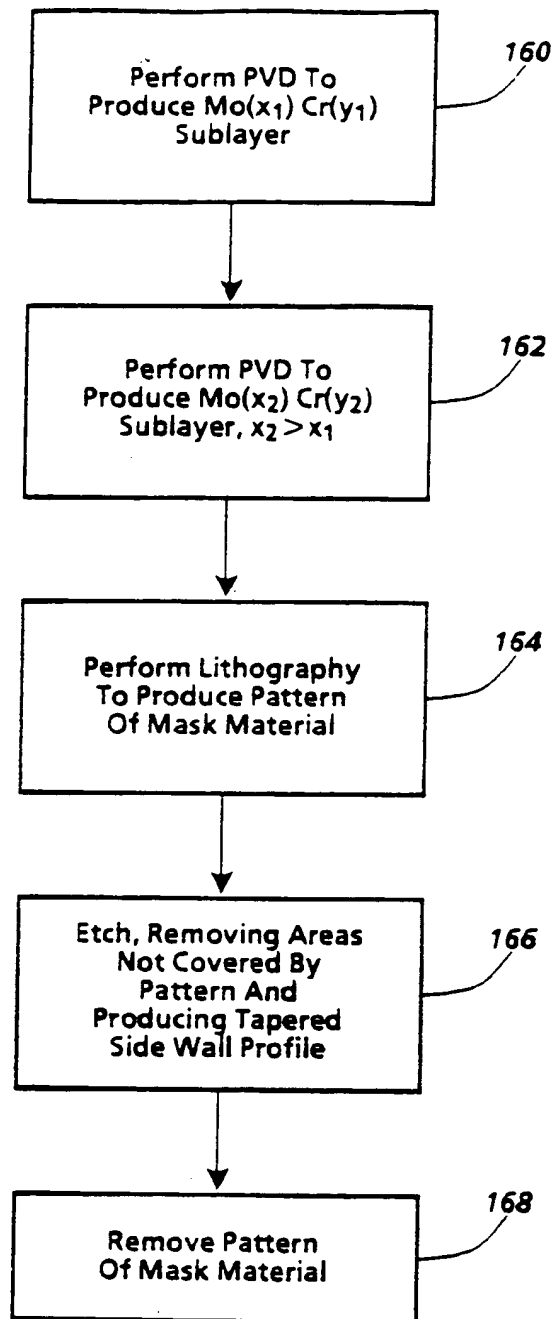


**Fig. 6**

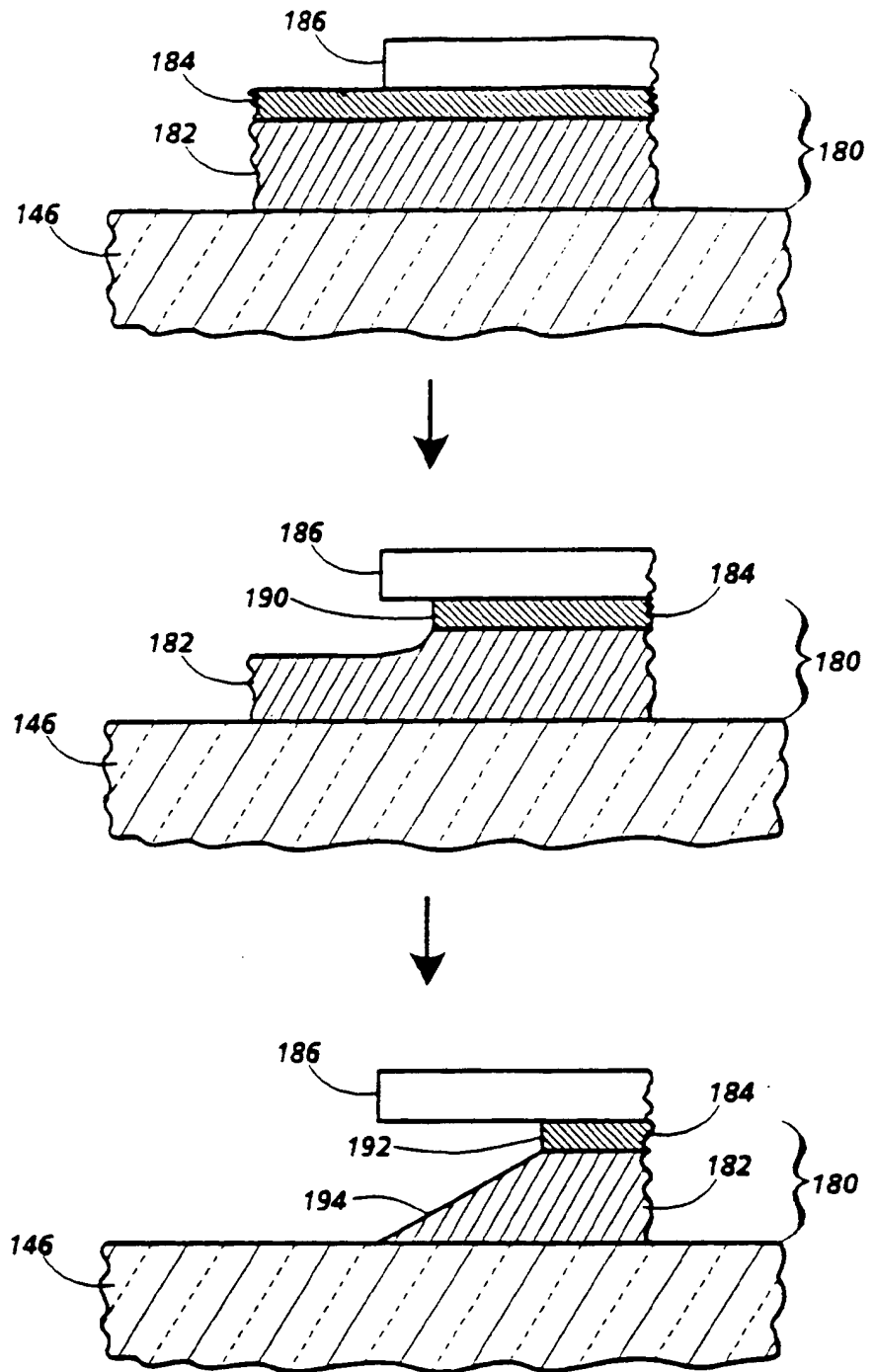


**Fig. 7**

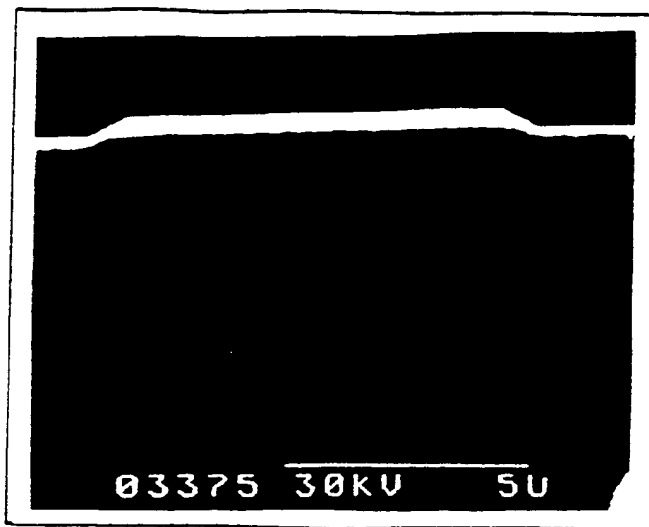
**Fig. 8****Fig. 9**

**Fig.10**

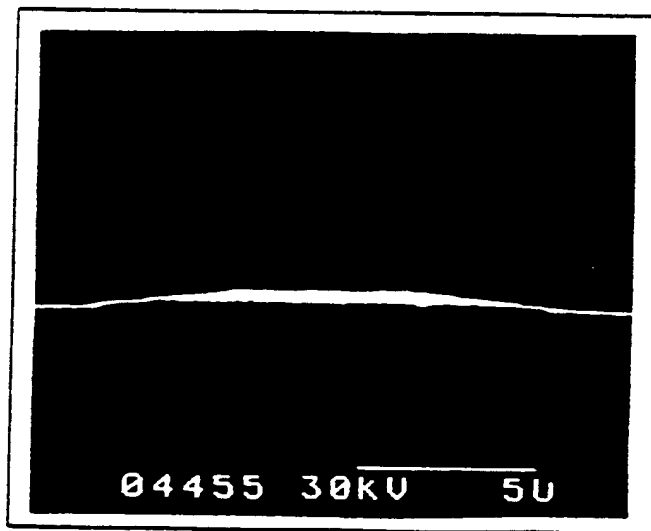




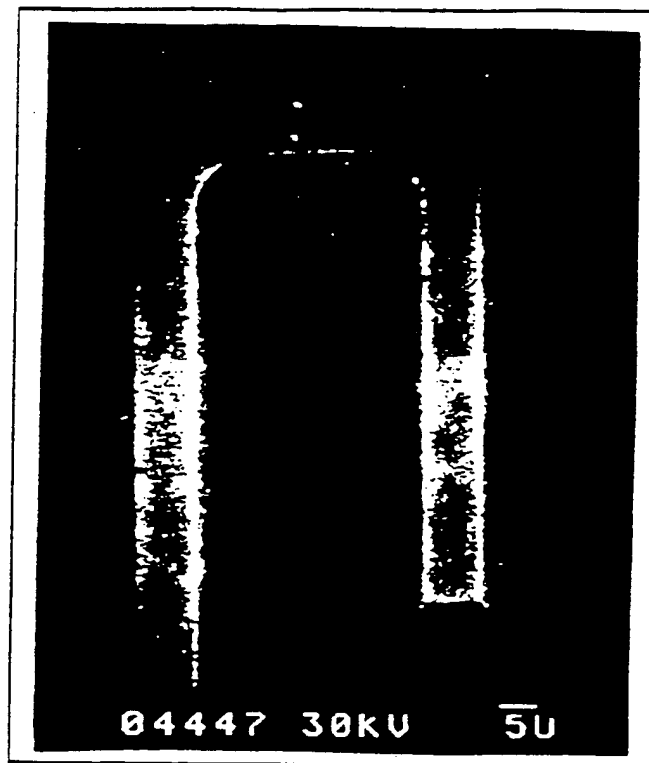
**Fig.11**



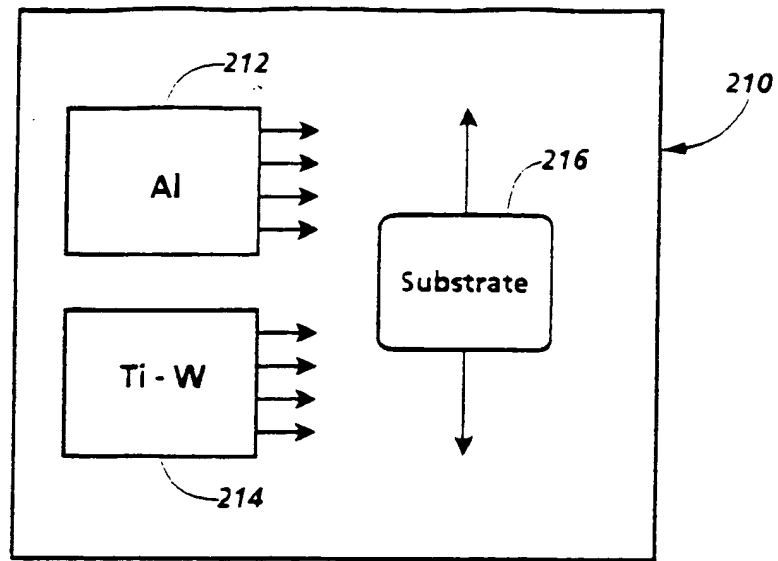
*Fig. 12*



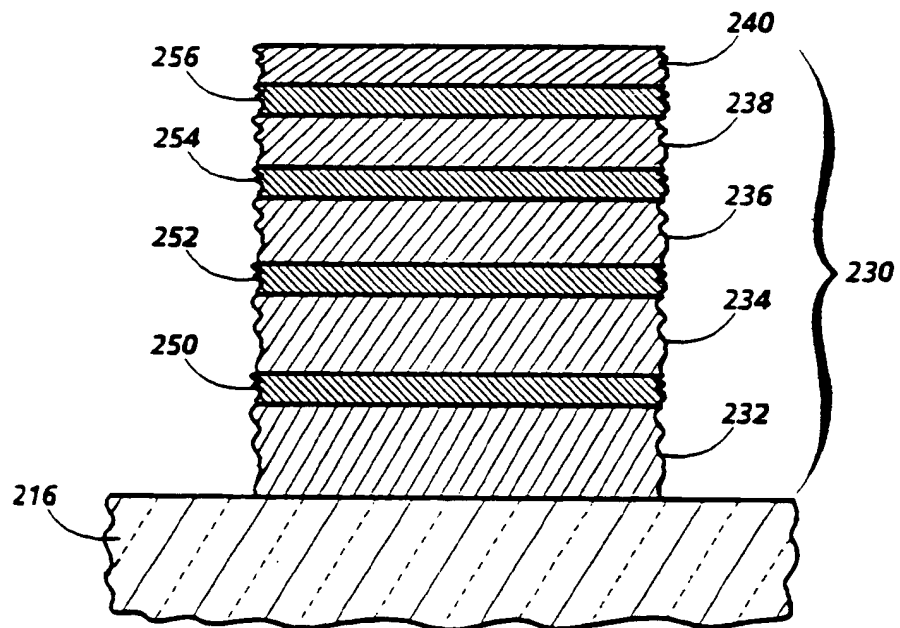
*Fig. 13*



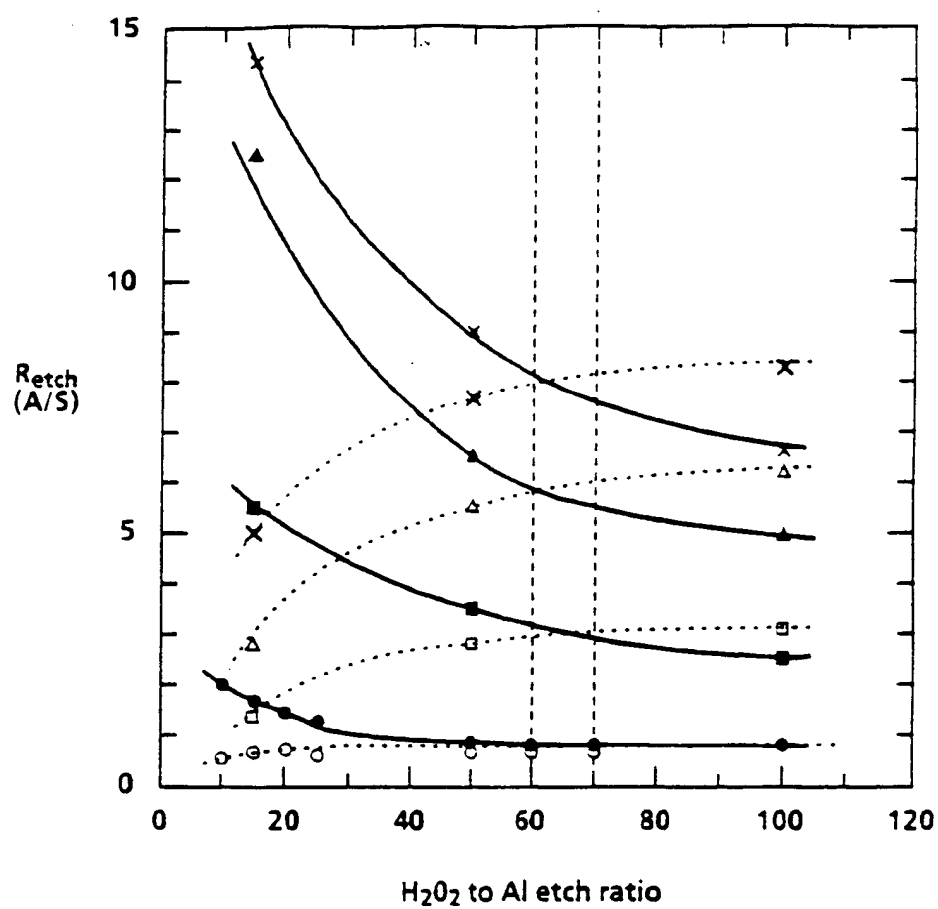
**Fig. 14**



**Fig.15**

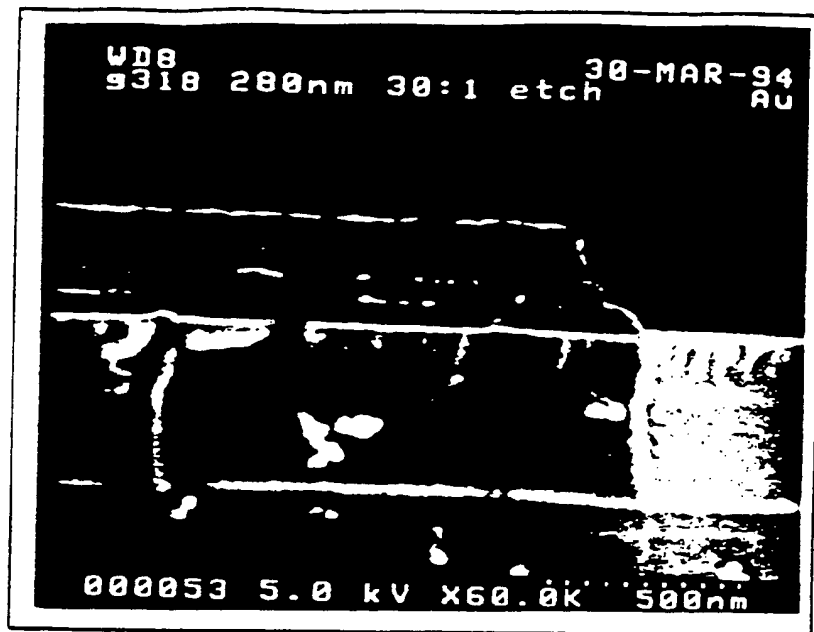


**Fig.16**

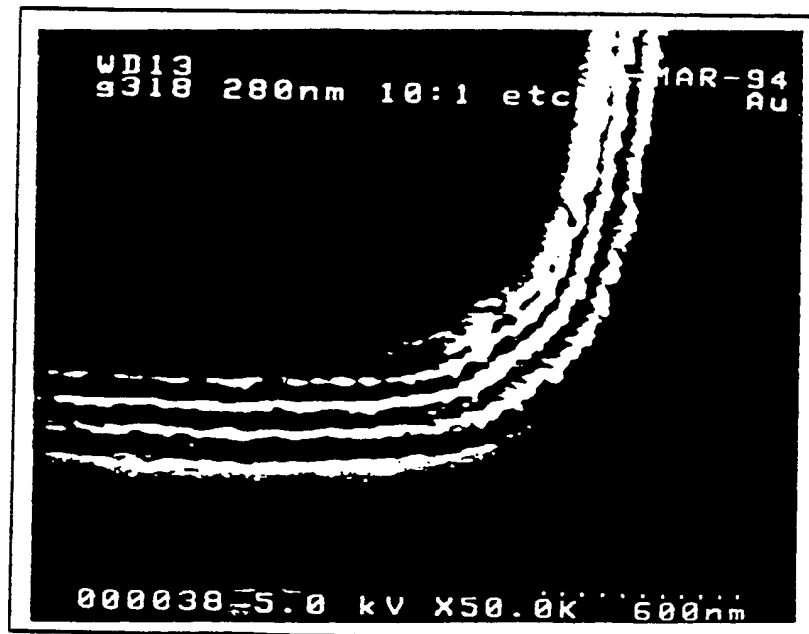


Al 23C	●
TiW 23C	○
Al 35C	■
TiW 35C	□
Al 45C	▲
TiW 45C	△
Al 50C	×
TiW 50C	×

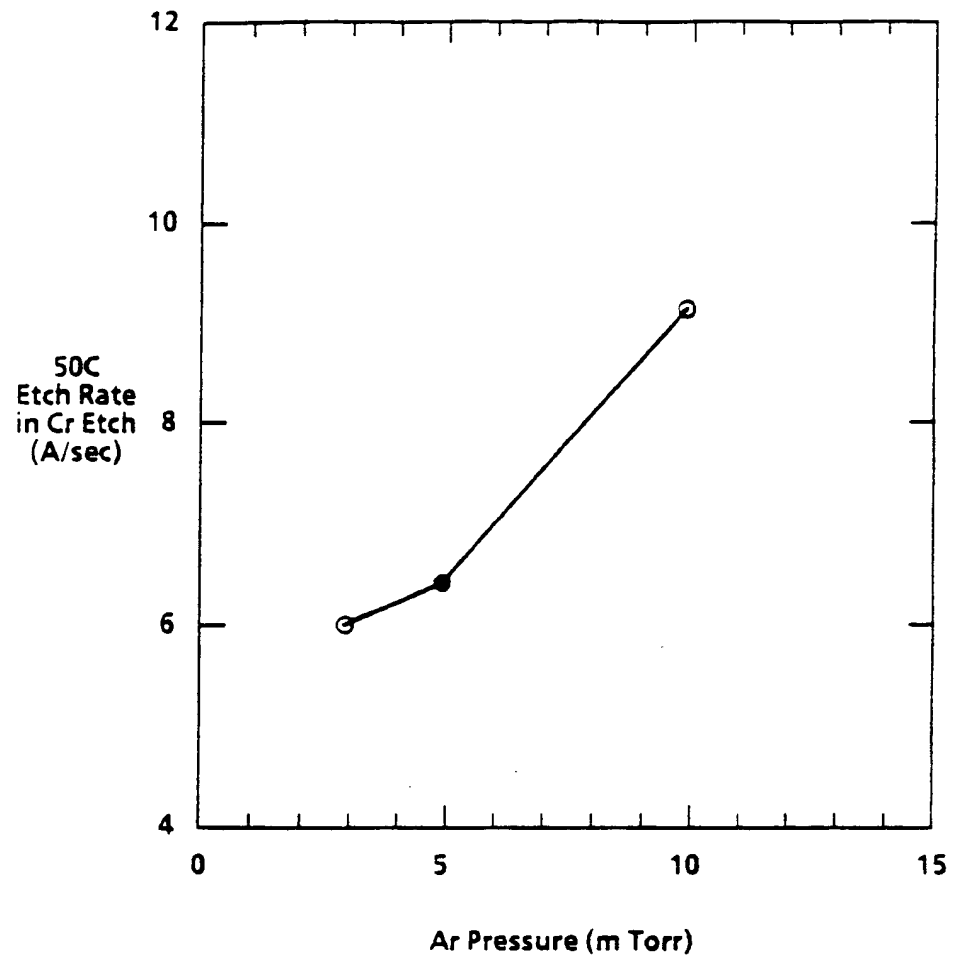
**Fig.17**

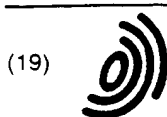


*Fig. 18*



*Fig. 19*

**Fig. 20**



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(11)

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(12)

## EUROPEAN PATENT APPLICATION

(88) Date of publication A3:  
27.12.1996 Bulletin 1996/52

(51) Int Cl.<sup>5</sup>: H01L 21/321, G02F 1/133

(43) Date of publication A2:  
02.11.1995 Bulletin 1995/44

(21) Application number: 95302614.3

(22) Date of filing: 19.04.1995

(84) Designated Contracting States:  
DE FR GB

(30) Priority: 28.04.1994 US 235010

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### (54) Thin-film structure tapered feature

(57) A feature (18; Fig. 1) in a thin-film structure (16; Fig. 1) such as an AMLCD array (Fig. 6) has an edge with a tapered sidewall profile (24; Fig. 1), reducing step coverage problems. The method of forming the feature includes producing (30) a layer in which local etch rates vary in the thickness direction of the layer. The layer can then be etched (34) to produce the feature with the tapered sidewall profile. The layer can be produced by physical vapor deposition. The layer can, for example, include sublayers with different etch rates (Fig. 9), either due to different atomic proportions of constituents or due to different etchants. Or local etch rates can vary continuously as a result of changing deposition conditions. Differences in etch rates or differences in etchant mixtures can be used to obtain a desired angle of elevation.

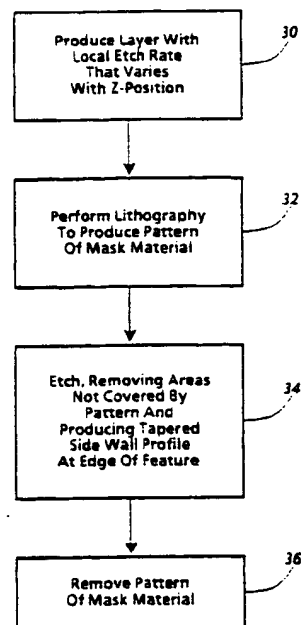


Fig. 5

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# EUROPEAN SEARCH REPORT

Application Number  
EP 95 30 2614

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
X	US-A-4 181 564 (FOGARTY ET AL) 1 January 1980 * claim 1 *	1,9	H01L21/321 G02F1/133
X	US-A-5 007 984 (MITSUBISHI) 16 April 1991 * claims *	1,2,6	
X	DE-A-39 14 602 (ROBERT BOSCH) 8 November 1990 * claims *	1,2,5	
X	US-A-4 543 707 (ITO ET AL) 1 October 1985 * claims *	1,2,4,5, 7,9	
X	PATENT ABSTRACTS OF JAPAN vol. 5, no. 44 (E-050), 24 March 1981 & JP-A-56 001538 (MITSUBISHI), 9 January 1981, * abstract *	1-3	
X	US-A-4 938 841 (SHAHAR ET AL) 3 July 1990 * column 4, line 56 *	1,3,5	TECHNICAL FIELDS SEARCHED (Int.Cl.6) H01L
X	EP-A-0 570 205 (SHARP) 18 November 1993 * figures *	10	
A	DIGEST OF THE 1989 SID INT. SYMP., BALTIMORE, USA, 16 - 18 May 1989, pages 226-229, XP000076868 ICHIKAWA ET AL: "14.3-in. diagonal 16 color TFT-LCD panel using a-Si:H TFTs" * page 227, left-hand column, paragraph 2 *	10	
-/--			
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 15 October 1996	Examiner Gori, P
<p><b>CATEGORY OF CITED DOCUMENTS</b></p> <p>X : particularly relevant if taken alone Y : particularly relevant if combined with another document of the same category A : technological background O : non-written disclosure P : intermediate document</p> <p>T : theory or principle underlying the invention E : earlier patent document, but published on, or after the filing date D : document cited in the application I : document cited for other reasons - : member of the same patent family, corresponding document</p>			

EPO FORM 1503 01.82 (P04C01)



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# EUROPEAN SEARCH REPORT

Application Number  
EP 95 30 2614

DOCUMENTS CONSIDERED TO BE RELEVANT			
Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.6)
E	EP-A-0 660 381 (PHILIPS ELECTRONICS) 28 June 1995 * the whole document *	1-3,5,6,9,10	
A	WO-A-92 06505 (GENERAL ELECTRIC) 16 April 1992 * abstract *	10	
			TECHNICAL FIELDS SEARCHED (Int.Cl.6)
The present search report has been drawn up for all claims			
Place of search THE HAGUE		Date of completion of the search 15 October 1996	Examiner Gori, P
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